**Trimmed Offset Voltage:** 

TLC27L9 . . . 900 μV Max at 25°C,  $V_{DD} = 5 V$ 

- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over **Specified Temperature Range:**

 $0^{\circ}$ C to  $70^{\circ}$ C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- **Single-Supply Operation**
- **Common-Mode Input Voltage Range** Extends Below the Negative Rail (C-Suffix, **I-Suffix Types)**
- Ultra-Low Power . . . Typically 195 μW at 25°C,  $V_{DD} = 5 V$
- **Output Voltage Range includes Negative** Rail
- High Input Impedance . . .  $10^{12} \Omega$  Typ
- **ESD-Protection Circuitry**
- **Small-Outline Package Option Also** Available in Tape and Reel
- **Designed-In Latch-Up Immunity**

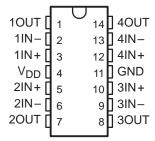
#### description

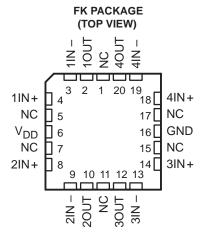
The TLC27L4 and TLC27L9 quad operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, extremely low power, and high gain.

These devices use Texas instruments silicon-gate LinCMOS™ technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and low-power consumption make these cost-effective devices ideal for high-gain, low- frequency, low-power applications. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27L4 (10 mV) to the high-precision TLC27L9 (900  $\mu$ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

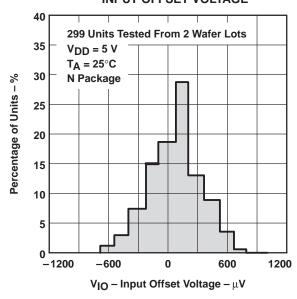
#### D, J, N, OR PW PACKAGE (TOP VIEW)





NC - No internal connection

#### **DISTRIBUTION OF TLC27L9** INPUT OFFSET VOLTAGE



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#### description (continued)

In general, many features associated with bipolar technology are available on LinCMOS™ operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27L4 and TLC27L9. The devices also exhibit low voltage single-supply operation and ultra-low power consumption, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand –100-mA surge currents without sustaining latch-up.

The TLC27L4 and TLC27L9 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices, as exposure to ESD may result in the degradation of the device parametric performance.

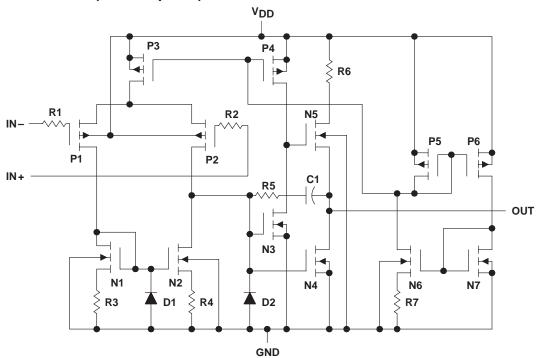
The C-suffix devices are characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C. The I-suffix devices are characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C. The M-suffix devices are characterized for operation from  $-55^{\circ}$ C to  $125^{\circ}$ C.

#### **AVAILABLE OPTIONS**

			PA	CKAGED DEVIC	ES		CHIP
TA	V <sub>IO</sub> max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	FORM (Y)
	900 μV	TLC27L9CD	_	_	TLC27L9CN	_	_
0°C to 70°C	2 mV	TLC27L4BCD	_	_	TLC27L4BCN	_	_
0 0 10 70 0	5 mV	TLC27L4ACD	_	_	TLC27L4ACN	_	_
	10 mV	TLC27L4CD	_	_	TLC27L4CN	TLC27L4CPW	TLC27L4Y
	900 μV	TLC27L9ID	_	_	TLC27L9IN	_	_
-40°C to 85°C	2 mV	TLC27L4BID	_	_	TLC27L4BIN	_	_
-40 C to 65 C	5 mV	TLC27L4AID	_	_	TLC27L4AIN	_	_
	10 mV	TLC27L4ID	_	_	TLC27L4IN	_	_
-55°C to 125°C	900 μV	TLC27L9MD	TLC27L9MFK	TLC27L9MJ	TLC27L9MN	_	_
-55 C to 125 C	10 mV	TLC27L4MD	TLC27L4MFK	TLC27L4MJ	TLC27L4MN	_	_

The D package is available taped and reeled. Add R suffix to the device type (e.g., TLC27L9CDR).

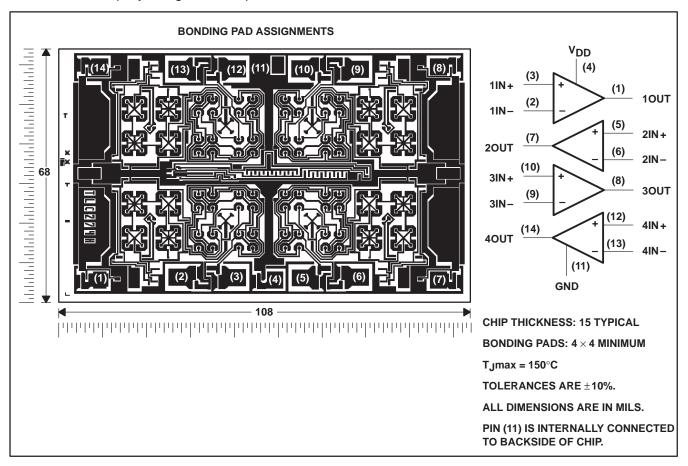
### equivalent schematic (each amplifier)



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#### TLC27L4Y chip information

These chips, when properly assembled, display characteristics similar to the TLC27L4C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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### absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V <sub>DD</sub> (see Note 1)	
Differential input voltage, V <sub>ID</sub> (see Note 2)	
Input voltage range, V <sub>I</sub> (any input)	
Input current, I <sub>I</sub>	
Output current, IO (each output)	±30 mA
Total current into V <sub>DD</sub>	
Total current out of GND	45 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Continuous total dissipation	,
Operating free-air temperature, T <sub>A</sub> : C suffix	,
Operating free-air temperature, T <sub>A</sub> : C suffix	0°C to 70°C
Operating free-air temperature, T <sub>A</sub> : C suffix	
Operating free-air temperature, T <sub>A</sub> : C suffix	
Operating free-air temperature, T <sub>A</sub> : C suffix	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
  - 2. Differential voltages are at IN+ with respect to IN-.
  - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
N	1575 mW	12.6 mW/°C	1008 mW	819 mW	_
PW	700 mW	5.6 mW/°C	448 mW	_	_

#### recommended operating conditions

		C SU	FFIX	I SUI	FFIX	M SU	FFIX	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>		3	16	4	16	4	16	V
Common-mode input voltage, V <sub>IC</sub>	V <sub>DD</sub> = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, v <sub>IC</sub>	V <sub>DD</sub> = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C



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### electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T <sub>A</sub> †	TL TL	.C27L4( .C27L4 <i>I</i> .C27L4E .C27L9(	AC BC	UNIT
						MIN	TYP	MAX	
		TLC27L4C	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC27L4C	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			12	mV
		TLC27L4AC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TLO27L4AC	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			6.5	
1 10	input onset voltage	TLC27L4BC		$V_{IC} = 0$ ,	25°C		240	2000	
		TLC27L4BC	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L9C	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0$ ,	25°C		200	900	μν
		TLC27L9C	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			1500	
ανιο	Average temperature coef offset voltage	ficient of input			25°C to 70°C		1.1		μV/°C
			V 0.5.V	.,	25°C		0.1		_
10	Input offset current (see N	ote 4)	$V_0 = 2.5 V$ ,	$V_{IC} = 2.5 \text{ V}$	70°C		7	300	pA
			.,		25°C		0.6		
IВ	Input bias current (see No	te 4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	70°C		40	600	pA
	Common mode input volta	ige range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	ge range			Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	0°C	3	4.1		V
					70°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	50	520		
A <sub>VD</sub>	Large-signal differential vo amplification	oltage	$V_0 = 2.5 \text{ V to 2 V},$	$R_L = 1 M\Omega$	0°C	50	680		V/mV
	amplification				70°C	50	380		
					25°C	65	94		
CMRR	Common-mode rejection r	atio	V <sub>IC</sub> = V <sub>ICR</sub> min		0°C	60	95		dB
					70°C	60	95		
	0 1 1 1				25°C	70	97		
ksvr	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{IO})$	atio	$V_{DD} = 5 V \text{ to } 10 V,$	$V_0 = 1.4 \ V$	0°C	60	97		dB
	(— , OO, — , IO)				70°C	60	98		
			V- 0.5.V	V/- 0.5.V	25°C		40	68	
IDD	Supply current (four ampli	fiers)	V <sub>O</sub> = 2.5 V, No load	$V_{IC} = 2.5 V,$	0°C		48	84	μΑ
					70°C		31	56	

<sup>†</sup> Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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## electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T <sub>A</sub> †	TI TI	.C27L4C .C27L4A .C27L4E .C27L9C	C SC	UNIT
						MIN	TYP	MAX	
		TLC27L4C	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		TLC27L4C	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			12	mV
		TI C271 4AC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	IIIV
V. 0	Input offset voltage	TLC27L4AC	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			6.5	
VIO	input onset voitage	TLC27L4BC	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		260	2000	
		TEC27E4BC	$R_S = 50 \Omega$	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L9C	$V_0 = 1.4 V$ ,	$V_{IC} = 0$ ,	25°C		210	1200	μν
		12027230	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			1900	
αVIO	Average temperature co input offset voltage	efficient of			25°C to 70°C		1		μV/°C
li o	Input offset current (see	Note 4)	V <sub>O</sub> = 5 V,	V <sub>IC</sub> = 5 V	25°C		0.1		pА
ΙΟ	input onset current (see	Note 4)	V() = 5 V,	VIC = 2 V	70°C		7	300	pΑ
1.5	Input bias current (see N	loto 4)	V <sub>O</sub> = 5 V,	V <sub>IC</sub> = 5 V	25°C		0.7		pА
ΙΒ	input bias current (see N	10te 4)	V() = 5 V,	VIC = 2 V	70°C		50	600	PΑ
	Common-mode input vo	Itage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 8.5			V
					25°C	8	8.9		
Vон	High-level output voltage	•	$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	0°C	7.8	8.9		V
					70°C	7.8	8.9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOL = 0	0°C		0	50	mV
					70°C		0	50	
	Lawrence and all the second at	11			25°C	50	870		
AVD	Large-signal differential amplification	voitage	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	0°C	50	1020		V/mV
					70°C	50	660		
					25°C	65	97		
CMRR	Common-mode rejection	ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		0°C	60	97		dB
					70°C	60	97		
	Supply-voltage rejection	ratio			25°C	70	97		
ksvr	Supply-voltage rejection (ΔVDD/ΔVIO)	IallU	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \ V$	0°C	60	97		dB
					70°C	60	98		
			\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	V <sub>IC</sub> = 5 V,	25°C		57	92	
$I_{DD}$	Supply current (four amp	olifiers)	V <sub>O</sub> = 5 V, No load	A IC = 2 A'	0°C		72	132	μΑ
					70°C		44	80	

Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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### electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST COND	DITIONS	T <sub>A</sub> †	TL TL	.C27L4I .C27L4 <i>I</i> .C27L4E .C27L9I	AI BI	UNIT
		_				MIN	TYP	MAX	
		TLC27L4I	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	
		12027241	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			13	mV
		TLC27L4AI	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TLC27L4AI	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			7	
1 10	input onset voltage	TLC27L4BI		V <sub>IC</sub> = 0,	25°C		240	2000	
		TEG27E4BI	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			3500	μV
		TLC27L9I	$V_0 = 1.4 V,$	$V_{IC} = 0$ ,	25°C		200	900	μν
		TEOZYESI	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			2000	
ανιο	Average temperature coeffoffset voltage	fficient of input			25°C to 85°C		1.1		μV/°C
	lanut effect compant (a.e. b)	lata 4)	V 05V	V 0.5.V	25°C		0.1		- ^
lio	Input offset current (see N	iote 4)	$V_0 = 2.5 V$ ,	$V_{IC} = 2.5 V$	85°C		24	1000	pΑ
	Land Range and Anna Na	(- 4)	V 05V		25°C		0.6		A
ΙΒ	Input bias current (see No	ite 4)	$V_0 = 2.5 V$ ,	$V_{IC} = 2.5 V$	85°C		200	2000	pΑ
	Common-mode input volta	age range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	.go (ago			Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	-40°C	3	4.1		V
					85°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	50	480		
$A_{VD}$	Large-signal differential vo amplification	oltage	$V_O = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	-40°C	50	900		V/mV
	ampimoation				85°C	50	330		
					25°C	65	94		
CMRR	Common-mode rejection i	ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		−40°C	60	95		dB
					85°C	60	95		
	Ourant and the	- 0 -			25°C	70	97		
ksvr	Supply-voltage rejection re $(\Delta V_{DD}/\Delta V_{IO})$	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	-40°C	60	97		dB
	·-··ΠΟ/				85°C	60	98		
			V- 25V	V:- 25V	25°C		39	68	
$I_{DD}$	Supply current (four ampli	fiers)	V <sub>O</sub> = 2.5 V, No load	$V_{IC} = 2.5 V,$	-40°C		62	108	μΑ
					85°C		29	52	

<sup>†</sup>Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



<sup>5.</sup> This range also applies to each input individually.

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## electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T <sub>A</sub> †	TI TI TI	_C27L4I _C27L4 <i>I</i> _C27L4E _C27L9I	AI BI	UNIT
		1				MIN	TYP	MAX	
		TLC27L4I	V <sub>O</sub> = 1.4 V,	$V_{IC} = 0$ ,	25°C		1.1	10	
			$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			13	mV
		TLC27L4AI	$V_{O} = 1.4 \text{ V},$ RS = 50 $\Omega$ ,	$V_{IC} = 0$ , $R_L = 1 M\Omega$	25°C	<u> </u>	0.9	5	
VIO	Input offset voltage		<u> </u>		Full range	<u> </u>		7	
		TLC27L4BI	$V_O = 1.4 \text{ V},$ $R_S = 50 \Omega,$	$V_{IC} = 0$ , $R_L = 1 M\Omega$	25°C		260	2000	
			<u> </u>		Full range	<u> </u>	040	3500	μV
		TLC27L9I	$V_O = 1.4 \text{ V},$ $R_S = 50 \Omega,$	$V_{IC} = 0$ , $R_{L} = 1 M\Omega$	25°C		210	1200	
	Average temperature coef	ficient of innut	113 = 00 32,	11 - 1 11122	Full range 25°C to		-	2900	
αVIO	Average temperature coef offset voltage	licient of input			85°C		1		μV/°C
					25°C		0.1		
10	Input offset current (see N	ote 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$	85°C		26	1000	pΑ
			., .,	., -,,	25°C		0.7		
lВ	Input bias current (see No	te 4)	V <sub>O</sub> = 5 V,	$V_{IC} = .5 V$	85°C		220	2000	pΑ
	Common-mode input volta	age range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	go rango			Full range	-0.2 to 8.5			V
					25°C	8	8.9		
VOH	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	−40°C	7.8	8.9		V
					85°C	7.8	8.9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−40°C		0	50	mV
					85°C		0	50	
					25°C	50	800		
AVD	Large-signal differential vo amplification	ltage	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	−40°C	50	1550		V/mV
	apoation				85°C	50	585		
					25°C	65	97		
CMRR	Common-mode rejection r	atio	V <sub>IC</sub> = V <sub>ICR</sub> min		−40°C	60	97		dB
					85°C	60	98		
	Cumply voltages relienting				25°C	70	97		
ksvr	Supply-voltage rejection ra $(\Delta V_{DD}/\Delta V_{IO})$	auo	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \ V$	−40°C	60	97		dB
					85°C	60	98		
			V = F V	\\ \(\bar{\bar{\bar{\bar{\bar{\bar{\bar{	25°C		57	92	
$I_{DD}$	Supply current (four ampli	fiers)	V <sub>O</sub> = 5 V, No load	$V_{IC} = 5 V$ ,	−40°C		98	172	μΑ
					85°C		40	72	

<sup>†</sup>Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



<sup>5.</sup> This range also applies to each input individually.

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### electrical characteristics at specified free-air temperature, V<sub>DD</sub> = 5 V (unless otherwise noted)

	PARAMETER		TEST CONE	DITIONS	T <sub>A</sub> †		.C27L4N .C27L9N		UNIT
						MIN	TYP	MAX	
		TI COZI 4M	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	>/
	Lancet office to college	TLC27L4M	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			12	mV
VIO	Input offset voltage	TI 0071 014	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		200	900	
		TLC27L9M	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			3750	μV
ανιο	Average temperature coeff offset voltage	ficient of input			25°C to 125°C		1.4		μV/°C
	Leavet effect comment (e.e. N	-1- 4)	V 05V	., 0.5.	25°C		0.1		рΑ
IIO	Input offset current (see No	ote 4)	$V_0 = 2.5 V$ ,	$V_{IC} = 2.5 V$	125°C		1.4	15	nA
			.,		25°C		0.6		pА
ΙΒ	Input bias current (see Not	te 4)	$V_0 = 2.5 V$ ,	$V_{IC} = 2.5 V$	125°C		9	35	nA
V	Common-mode input volta	ige range			25°C	-0.2 to 4	-0.3 to 4.2		٧
VICR	(see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	−55°C	3	4.1		V
					125°C	3	4.2		
					25°C		0	50	
$V_{OL}$	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
					25°C	50	480		
$A_{VD}$	Large-signal differential vo amplification	ltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	−55°C	25	950		V/mV
	ampimoation				125°C	25	200		
					25°C	65	94		
CMRR	Common-mode rejection ra	atio	$V_{IC} = V_{ICR}min$		−55°C	60	95		dB
					125°C	60	85		
	0 1 1/2				25°C	70	97		
ksvr	Supply-voltage rejection ra (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \ V$	−55°C	60	97		dB
	\\U\'\_\I\\/				125°C	60	98		
				.,	25°C		39	68	
$I_{DD}$	Supply current (four amplif	fiers)	V <sub>O</sub> = 2.5 V, No load	$V_{IC} = 2.5 V,$	−55°C		69	120	μΑ
			110.000		125°C		27	48	

† Full range is -55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

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## electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	TAT		.C27L4N .C27L9N		UNIT
						MIN	TYP	MAX	
		TLC27L4M	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		1.1	10	\/
.,	land offert valtage	TLC27L4IVI	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			12	mV
VIO	Input offset voltage	TI 0071 014	V <sub>O</sub> = 1.4 V,	V <sub>IC</sub> = 0,	25°C		210	1200	\/
		TLC27L9M	$R_S = 50 \Omega$ ,	$R_L = 1 M\Omega$	Full range			4300	μV
ανιο	Average temperature coeffinput offset voltage	ficient of			25°C to 125°C		1.4		μV/°C
	land offert company (see A	lata 4\	V- 5V	\/ F\/	25°C		0.1		pА
lio	Input offset current (see N	iote 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$	125°C		1.8	15	nA
	lanut hina aumant (ann Na	4- 4)	V 5V	V 5.V	25°C		0.7		pА
lΒ	Input bias current (see No	te 4)	$V_0 = 5 V$ ,	$V_{IC} = 5 V$	125°C		10	35	nA
V	Common-mode input volta	age range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	0 to 8.5			V
					25°C	8	8.9		
∨он	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	−55°C	7.8	8.8		V
					125°C	7.8	9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOL = 0	−55°C		0	50	mV
					125°C		0	50	
					25°C	50	800		
$A_{VD}$	Large-signal differential vo amplification	oltage	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	−55°C	25	1750		V/mV
	apoatio				125°C	25	380		
					25°C	65	97		
CMRR	Common-mode rejection	atio	V <sub>IC</sub> = V <sub>ICR</sub> min		−55°C	60	97		dB
					125°C	60	91		
	Ourante de la contraction de l	- 1' -			25°C	70	97		
ksvr	Supply-voltage rejection ra (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \ V$	−55°C	60	97		dB
	(= · DD, = · 10)				125°C	60	98		
					25°C		57	92	
$I_{DD}$	Supply current (four ampli	fiers)	V <sub>O</sub> = 5 V, No load	AIC = 2A	−55°C		111	192	μΑ
					125°C		35	60	

†Full range is -55°C to 125°C.

NOTES: 4. The typical values of input bias current and Input offset current below 5 pA were determined mathematically.



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## electrical characteristics at specified free-air temperature, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

	PARAMETER	TEST CONI	OITIONS	TI	_C27L4\	′	UNIT
	FARAMETER	TEST CONI	DITIONS	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	$V_{O} = 1.4 \text{ V},$ $R_{S} = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 1 M\Omega$		1.1	10	mV
ανιο	Average temperature coefficient of input offset voltage	$T_A = 25^{\circ}C \text{ to } 70^{\circ}C$			1.1		μV/°C
IIO	Input offset current (see Note 4)	V <sub>O</sub> = 2.5 V,	V <sub>IC</sub> = 2.5 V		0.1		pА
I <sub>IB</sub>	Input bias current (see Note 4)	$V_0 = 2.5 V$ ,	V <sub>IC</sub> = 2.5 V		0.6		pА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 4	-0.3 to 4.2		٧
Vон	High-level output voltage	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	3.2	4.1		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I <sub>OL</sub> = 0		0	50	mV
AVD	Large-signal differential voltage amplification	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	50	520		V/mV
CMRR	Common-mode rejection ratio	V <sub>IC</sub> = V <sub>ICR</sub> min		65	94		dB
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	70	97		dB
I <sub>DD</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 2.5 V, No load	V <sub>IC</sub> = 2.5 V,		40	68	μΑ

## electrical characteristics at specified free-air temperature, $V_{DD}$ = 10 V, $T_A$ = 25°C (unless otherwise noted)

	PARAMETER	TEST CONI	OITIONE	Τι	_C27L4Y	′	UNIT
	PARAMETER	TEST CONI	DITIONS	MIN	TYP	MAX	UNII
VIO	Input offset voltage	$V_O = 1.4 \text{ V},$ $R_S = 50 \Omega,$	$V_{IC} = 0,$ $R_L = 1 M\Omega$		1.1	10	mV
ανιο	Average temperature coefficient of input offset voltage	$T_A = 25^{\circ}C$ to $70^{\circ}C$			1		μV/°C
IIO	Input offset current (see Note 4)	V <sub>O</sub> = 5 V,	$V_{IC} = 5 V$		0.1		рА
I <sub>IB</sub>	Input bias current (see Note 4)	$V_0 = 5 V$ ,	$V_{IC} = 5 V$		0.7		рА
VICR	Common-mode input voltage range (see Note 5)			-0.2 to 9	-0.3 to 9.2		V
Vон	High-level output voltage	V <sub>ID</sub> = 100 mV,	$R_L = 1 M\Omega$	8	8.9		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$	I <sub>OL</sub> = 0		0	50	mV
A <sub>VD</sub>	Large-signal differential voltage amplification	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	50	870		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$		65	97		dB
ksvr	Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V <sub>O</sub> = 1.4 V	70	97		dB
I <sub>DD</sub>	Supply current (four amplifiers)	V <sub>O</sub> = 5 V, No load	V <sub>IC</sub> = 5 V,		57	92	μА

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

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## operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L4C TLC27L4AC TLC27L4BC TLC27L9C			UNIT
					MIN	TYP	MAX	
				25°C		0.03		
			V <sub>IPP</sub> = 1 V	0°C		0.04		
SR	Claus rate at unity rain	$R_L = 1 M\Omega$ ,		70°C		0.03		\//v.o
J SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.03		V/μs
			V <sub>IPP</sub> = 2.5 V	0°C		0.03		
				70°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHZ, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
				25°C		5		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_I = 1 M\Omega,$	C <sub>L</sub> = 20 pF, See Figure 1	0°C		6		kHz
			Gee rigure r	70°C		4.5		
				25°C		85		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	0°C		100		kHz
, ·		occ rigare 3		70°C		65		
		1011	( 5	25°C		34°		
φm			f = B <sub>1</sub> , See Figure 3	0°C		36°		
		,		70°C		30°		

## operating characteristics at specified free-air temperature, $V_{DD}$ = 10 V

	PARAMETER	TEST CO	NDITIONS	т <sub>А</sub>	TLC27L4C TLC27L4AC TLC27L4BC TLC27L9C			UNIT
		ļ		2702	MIN	TYP	MAX	
				25°C		0.05		
		V <sub>IPP</sub> = 1 V 0°C 0.05						
SR	Slew rate at unity gain	$R_L = 1 M\Omega$ , $C_L = 20 pF$ ,		70°C		0.04		V/μs
	Siew rate at unity gain	See Figure 1		25°C		0.04		ν/μ3
			V <sub>IPP</sub> = 5.5 V	0°C		0.05		1
				70°C	0.04			1
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
		., .,		25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 1 M\Omega$ ,	C <sub>L</sub> = 20 pF,	0°C		1.3		kHz
		11( 1 10132,	oce rigare r	70°C		0.9		
				25°C		110		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	0°C		125		kHz
· 		Jose Figure 3		70°C		90		
	Phase margin	10 11		25°C		38°		
φm			f = B <sub>1</sub> , See Figure 3	0°C		40°		1
		- 20 p.,	23094.00	70°C		34°		1

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### operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L4I TLC27L4AI TLC27L4BI TLC27L9I			UNIT
					MIN	TYP	MAX	
				25°C		0.03		
			V <sub>IPP</sub> = 1 V	−40°C		0.04		
SR	Clay rate at unity gain	$R_L = 1 M\Omega$ ,		85°C		0.03		V/μs
J SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.03		ν/μδ
			V <sub>IPP</sub> = 2.5 V	−40°C		0.04		
				85°C		0.02		
Vn	Equivalent input noise voltage	f = 1 HZ, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
				25°C		5		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 1 M\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	−40°C		7		kHz
			Gee rigure r	85°C		4		
				25°C		85		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	−40°C		130		kHz
<u> </u>		Jee rigure 3		85°C		55		
	Phase margin	V 40 V	. 5	25°C		34°		
φm			f = B <sub>1</sub> , See Figure 3	−40°C		38°		
YIII		,	235gui 0 0	85°C		28°		

## operating characteristics at specified free-air temperature, $V_{DD}$ = 10 V

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L4I TLC27L4AI TLC27L4BI TLC27L9I			UNIT
					MIN	TYP	MAX	
				25°C		0.05		
			V <sub>IPP</sub> = 1 V	-40°C		0.06		
SR	Slow rate at unity gain	$R_L = 1 M\Omega$ ,		85°C		0.03		\//u0
J SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.04		V/μs
		ľ	V <sub>IPP</sub> = 2.5 V	−40°C	0.05			
				85°C		0.03		
Vn	Equivalent input noise voltage	f = 1 HZ, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
				25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 1 M\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1	−40°C		1.4		kHz
			See rigure r	85°C		0.8		
				25°C 110				
B <sub>1</sub>	Unity-gain bandwidth	$V_I = 10 \text{ mV}, \qquad C_L = 20 \text{ pF},$ See Figure 3		-40°C		155		kHz
		occ riguic o		85°C		80		
		10 11	. 5	25°C		38°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	−40°C		42°		
				85°C		32°		

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## operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	TA	T T	UNIT		
					MIN	TYP	MAX	
				25°C		0.03		
			V <sub>IPP</sub> = 1 V	−55°C		0.04		
SR	Clay rate at unity gain	$R_L = 1 M\Omega$ ,		125°C		0.02		1////
J SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.03		V/μs
			V <sub>IPP</sub> = 2.5 V	−55°C		0.04		
				125°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
				25°C		5		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 1 M\Omega$ ,		−55°C		8		kHz
		11( 1 10132,	occ rigure r	125°C		3		
		., ,, ,,		25°C		85		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	−55°C		140		kHz
		occ rigure 3		125°C		45		
		V 40V	4 D	25°C		34°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3	−55°C		39°		
		,	2221194100	125°C		25°		

## operating characteristics at specified free-air temperature, $V_{DD}$ = 10 V

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L4M TLC27L9M			UNIT
					MIN	TYP	MAX	
				25°C		0.05		
1			V <sub>IPP</sub> = 1 V	−55°C		0.06		
SR	Clay rate at unity gain	$R_L = 1 M\Omega$ ,		125°C		0.03		\//us
J SK	Slew rate at unity gain	C <sub>L</sub> = 20 pF, See Figure 1		25°C		0.04		V/μs
			V <sub>IPP</sub> = 5.5 V	−55°C		0.06		
				125°C		0.03		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,	25°C		70		nV/√ <del>Hz</del>
				25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_L = 1 M\Omega,$	C <sub>L</sub> = 20 pF, See Figure 1	−55°C		1.5		kHz
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	oco riguro r	125°C		0.7		
		.,,		25°C		110		
В1	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,	−55°C		165		kHz
		occ rigare o		125°C		70		
		\/. 40 m\/	4 D	25°C		38°		
φm	Phase margin	$V_{\parallel} = 10 \text{ mV},$ $C_{\parallel} = 20 \text{ pF},$	r = B <sub>1</sub> , See Figure 3	−55°C		43°		
		-C = 0   F · · · ·	2221.94.00	125°C		29°		

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## operating characteristics, $V_{DD}$ = 5 V, $T_A$ = 25°C

	PARAMETER	TEST CO	NDITIONS	TL	.C27L4Y	′	UNIT
	FARAMETER	1231 00	NDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$R_L = 1 M\Omega$ , $C_L = 20 pF$ ,	V <sub>IPP</sub> = 1 V		0.03		V/µs
SK	Siew rate at unity gain	See Figure 1	V <sub>IPP</sub> = 2.5 V		0.03		ν/μδ
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,		70		nV/√ <del>Hz</del>
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_L = 1 M\Omega,$	C <sub>L</sub> = 20 pF, See Figure 1		5		kHz
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	$C_L = 20 pF$ ,		85		kHz
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3		34°		

## operating characteristics, $V_{DD}$ = 10 V, $T_A$ = 25°C

	PARAMETER	TEST CO	NDITIONS	TL	.C27L4Y	<b>′</b>	UNIT
	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$R_L = 1 M\Omega$ , $C_L = 20 pF$ ,	V <sub>IPP</sub> = 1 V		0.05		V/µs
J Six	Siew rate at unity gain	See Figure 1	V <sub>IPP</sub> = 5.5 V		0.04		ν/μδ
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$ ,		70		nV/√ <del>Hz</del>
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 1 M\Omega$ ,	C <sub>L</sub> = 20 pF, See Figure 1		1		kHz
B <sub>1</sub>	Unity-gain bandwidth	V <sub>I</sub> = 10 mV, See Figure 3	C <sub>L</sub> = 20 pF,		110		kHz
фm	Phase margin	$V_I = 10 \text{ mV},$ $C_L = 20 \text{ pF},$	f = B <sub>1</sub> , See Figure 3		38°		

#### PARAMETER MEASUREMENT INFORMATION

#### single-supply versus split-supply test circuits

Because the TLC27L4 and TLC27L9 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

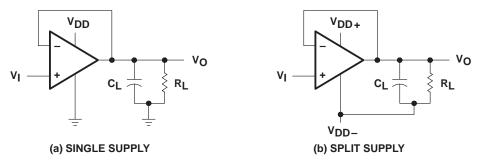


Figure 1. Unity-Gain Amplifier

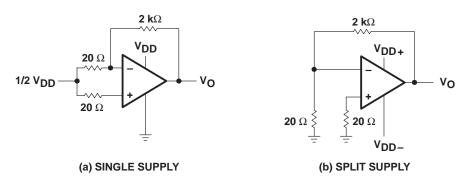


Figure 2. Noise-Test Circuit

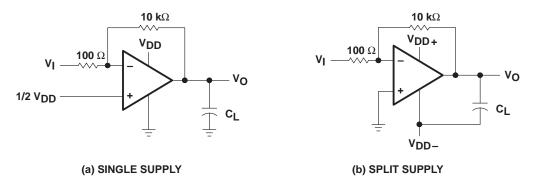


Figure 3. Gain-of-100 Inverting Amplifier

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#### PARAMETER MEASUREMENT INFORMATION

#### input bias current

Because of the high input impedance of the TLC27L4 and TLC27L9 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution: many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

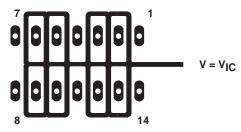


Figure 4. Isolation Metal Around Device Inputs (J and N packages)

#### low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.

#### input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.



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#### PARAMETER MEASUREMENT INFORMATION

#### full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

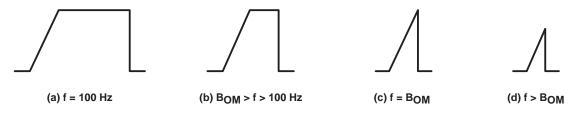


Figure 5. Full-Power-Response Output Signal

#### test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

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#### TYPICAL CHARACTERISTICS

#### **Table of Graphs**

			FIGURE
VIO	Input offset voltage	Distribution	6, 7
αVIO	Temperature coefficient	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
VOL	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I <sub>IB</sub> /I <sub>IO</sub>	Input bias and input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
IDD	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
В1	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
фm	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive loads	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
ф	Phase shift	vs Frequency	32, 33

#### TYPICAL CHARACTERISTICS

### **DISTRIBUTION OF TLC27L4 INPUT OFFSET VOLTAGE** 70 905 Amplifiers Tested From 6 Wafer Lots $V_{DD} = 5 V$ 60 $T_A = 25^{\circ}C$ N Package Percentage of Units – % 50 40 30 20 10 0 -5 -3 -2 -1 0

Figure 6

VIO - Input Offset Voltage - mV

**DISTRIBUTION OF TLC27L4 AND TLC27L9** 

**INPUT OFFSET VOLTAGE** 

#### **TEMPERATURE COEFFICIENT** 70 356 Amplifiers Tested From 8 Wafer Lots $V_{DD} = 5 V$ 60 T<sub>A</sub> = 25°C to 125°C N Package Percentage of Units – % 50 **Outliers:** (1) 19.2 μV/°C (1) 12.1 μV/°C 40 30 20 10 -10 -8 -6 -4 -20 2 6 10 $\alpha_{\mbox{VIO}}$ – Temperature Coefficient – $\mu\mbox{V}\slash\!\!/^{\circ}\mbox{C}$

Figure 8

DISTRIBUTION OF TLC27L4 INPUT OFFSET VOLTAGE

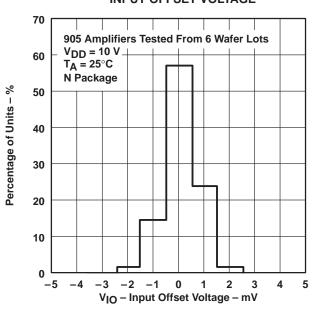


Figure 7

#### DISTRIBUTION OF TLC27L4 AND TLC27L9 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

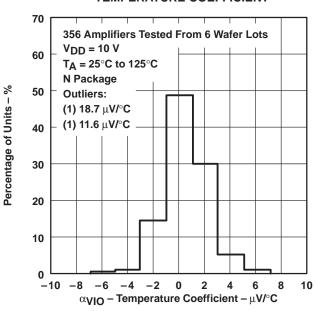


Figure 9

#### TYPICAL CHARACTERISTICS<sup>†</sup>

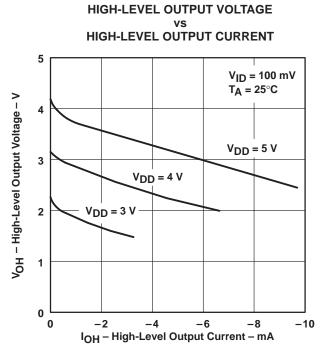
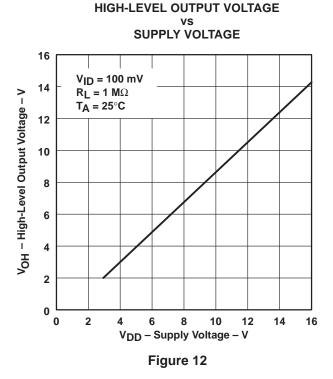


Figure 10



HIGH-LEVEL OUTPUT VOLTAGE VS HIGH-LEVEL OUTPUT CURRENT

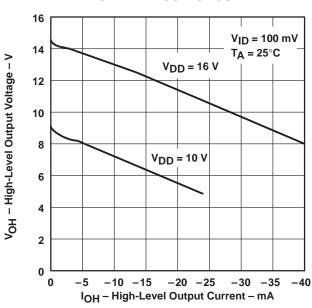
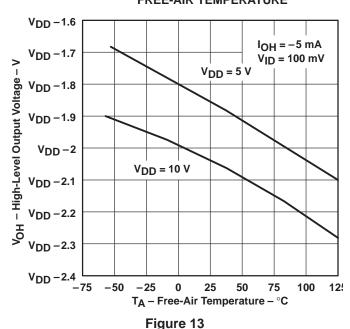


Figure 11

# HIGH-LEVEL OUTPUT VOLTAGE VS FREE-AIR TEMPERATURE



<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



#### TYPICAL CHARACTERISTICS†

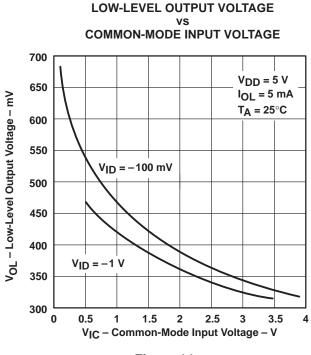
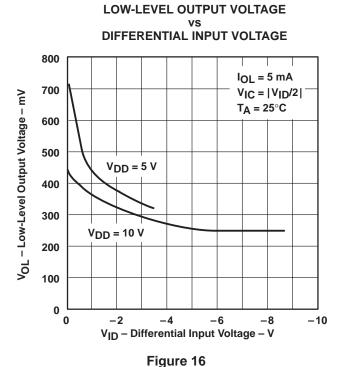


Figure 14



LOW-LEVEL OUTPUT VOLTAGE

vs

COMMON-MODE INPUT VOLTAGE

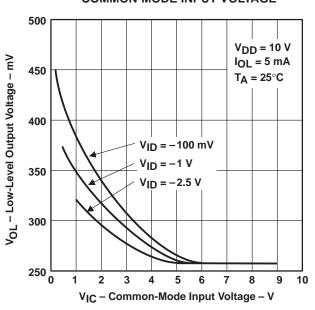


Figure 15

## LOW-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

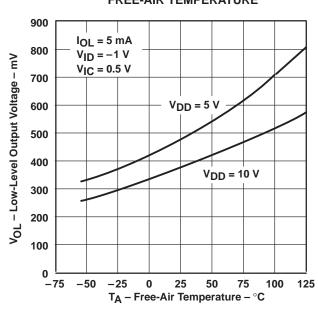
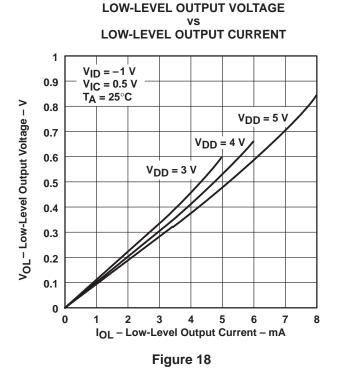


Figure 17

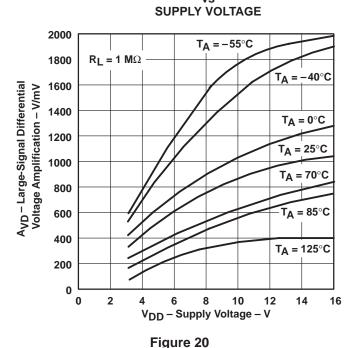
<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



#### TYPICAL CHARACTERISTICS<sup>†</sup>



LARGE-SIGNAL **DIFFERENTIAL VOLTAGE AMPLIFICATION** 



## **LOW-LEVEL OUTPUT VOLTAGE** LOW-LEVEL OUTPUT CURRENT

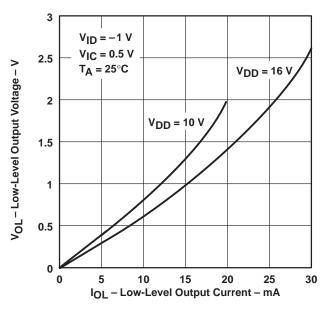


Figure 19

### LARGE-SIGNAL **DIFFERENTIAL VOLTAGE AMPLIFICATION** FREE-AIR TEMPERATURE

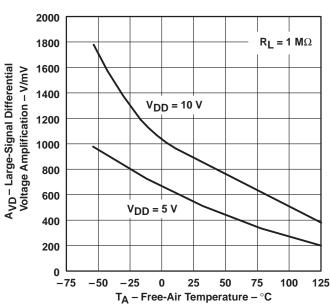


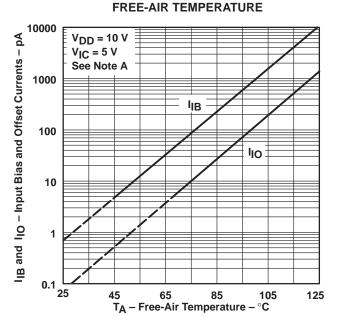
Figure 21

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



#### TYPICAL CHARACTERISTICS†

## INPUT BIAS CURRENT AND INPUT OFFSET CURRENT vs



NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

# COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT VS SUPPLY VOLTAGE

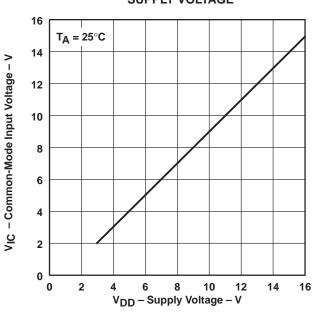
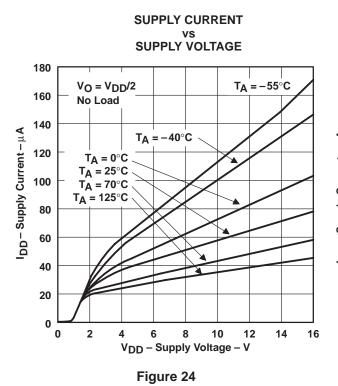


Figure 23

#### Figure 22



## SUPPLY CURRENT vs

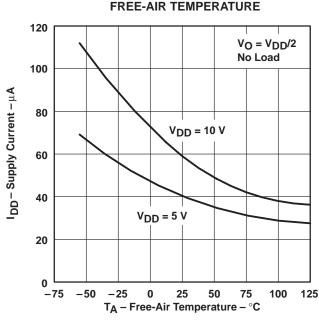
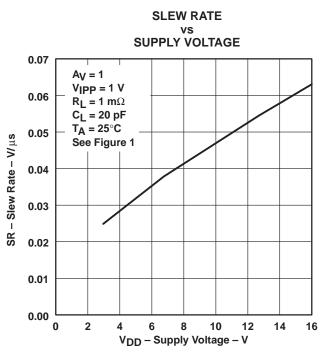


Figure 25

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

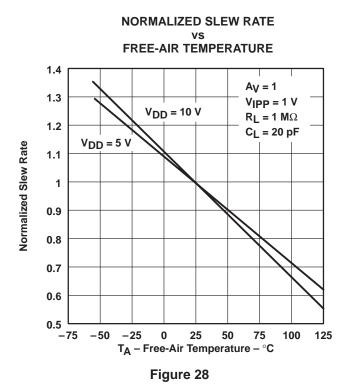
#### TYPICAL CHARACTERISTICS<sup>†</sup>



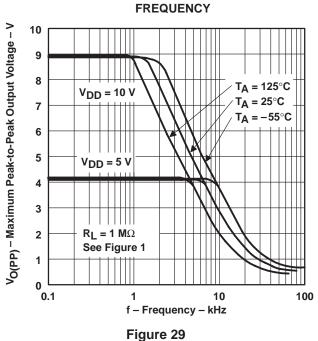
**SLEW RATE** vs FREE-AIR TEMPERATURE 0.07  $R_L = 1 M\Omega$  $V_{DD} = 10 V$  $C_L = 20 pF$ 0.06  $V_{IPP} = 5.5 V$  $A_V = 1$ See Figure 1 0.05 - Slew Rate - V/µs  $V_{DD} = 10 V$ V<sub>IPP</sub> = 1 V 0.04 0.03  $V_{DD} = 5 V$ 0.02 V<sub>IPP</sub> = 1 V  $V_{DD} = 5 V$ 0.01  $V_{IPP} = 2.5 V$ 0.00 75 -75 -50-2525 50 100 125  $T_A$  – Free-Air Temperature –  $^{\circ}C$ 

Figure 26





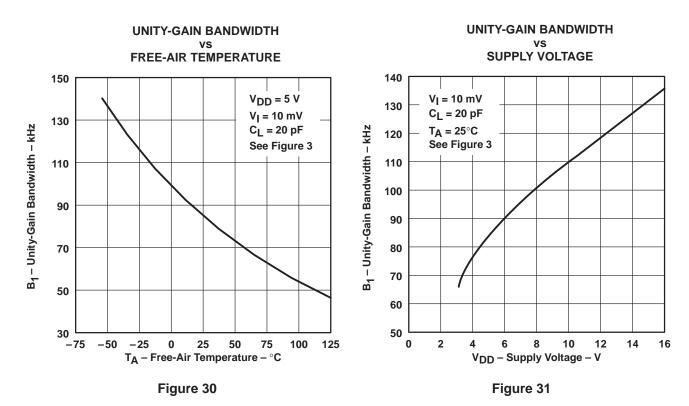
## MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE vs



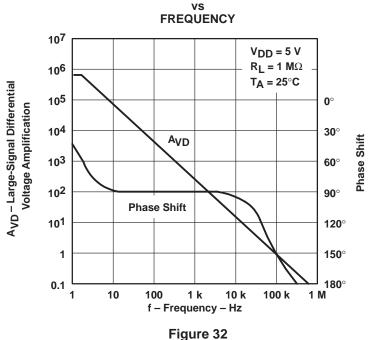
† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



#### TYPICAL CHARACTERISTICS†



## LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



#### TYPICAL CHARACTERISTICS<sup>†</sup>

#### LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VS

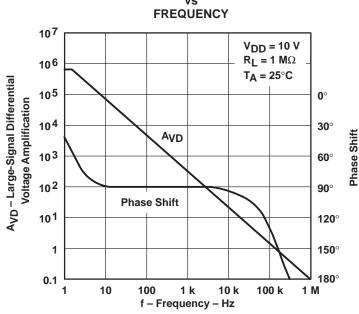
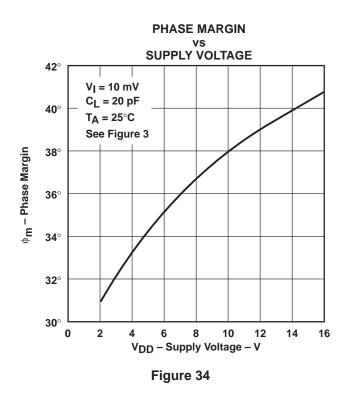


Figure 33



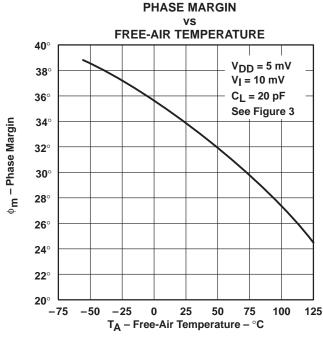


Figure 35

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

#### **TYPICAL CHARACTERISTICS**

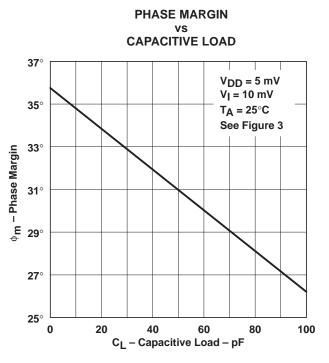
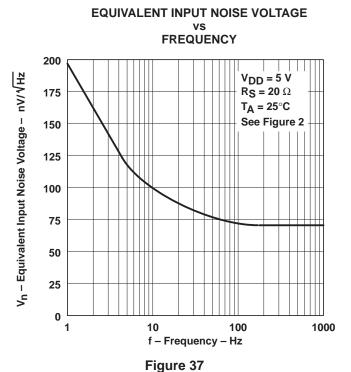


Figure 36



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#### single-supply operation

While the TLC27L4 and TLC27L9 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27L4 and TLC27L9 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27L4 and TLC27L9 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

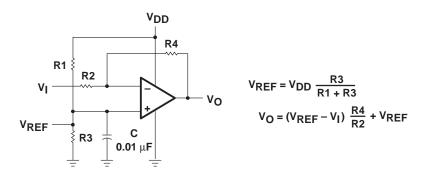
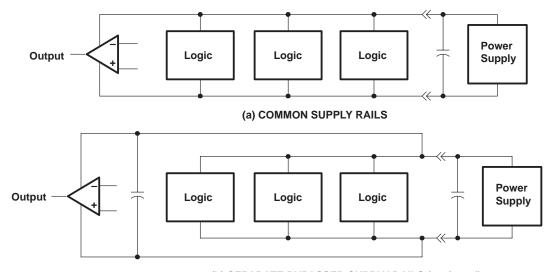


Figure 38. Inverting Amplifier With Voltage Reference

#### single-supply operation (continued)



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails

#### input characteristics

The TLC27L4 and TLC27L9 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at  $V_{DD}-1$  V at  $T_A=25$ °C and at  $V_{DD}-1.5$  V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27L4 and TLC27L9 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1  $\mu$ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27L4 and TLC27L9 are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

#### noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27L4 and TLC27L9 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k $\Omega$ , since bipolar devices exhibit greater noise currents.

#### noise performance (continued)

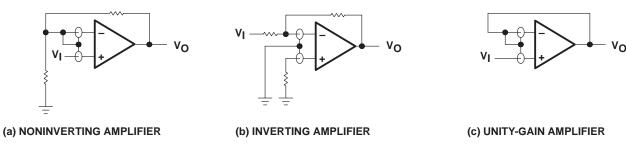
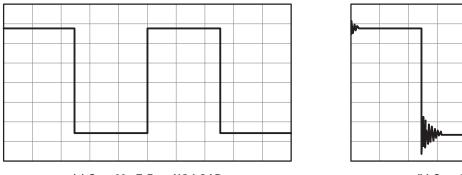


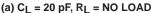
Figure 40. Guard-Ring Schemes

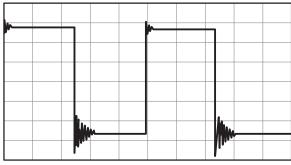
#### output characteristics

The output stage of the TLC27L4 and TLC27L9 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

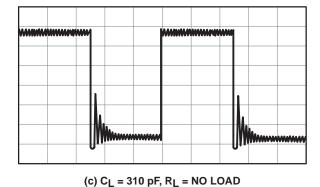
All operating characteristics of the TLC27L4 and TLC27L9 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.

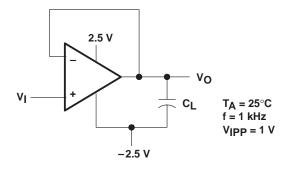






(b)  $C_L = 260 \text{ pF}$ ,  $R_L = NO \text{ LOAD}$ 





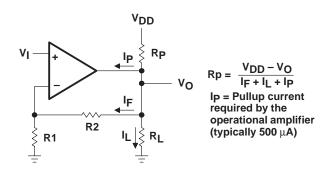
(d) TEST CIRCUIT

Figure 41. Effect of Capacitive Loads and Test Circuit



#### output characteristics (continued)

Although the TLC27L4 and TLC27L9 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (Rb) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately  $60~\Omega$  and  $180~\Omega$ , depending on how hard the operational amplifier input is driven. With very low values of Rp, a voltage offset from 0 V at the output occurs. Second, pullup resistor Rp acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.



v<sub>0</sub>

Figure 42. Resistive Pullup to Increase VOH

Figure 43. Compensation for Input Capacitance

#### feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

#### electrostatic discharge protection

The TLC27L4 and TLC27L9 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices, as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

#### latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27L4 and TLC27L9 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1  $\mu\text{F}$  typical) located across the supply rails as close to the device as possible.

#### latch-up (continued)

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

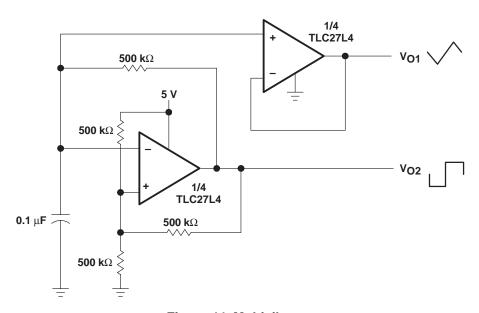
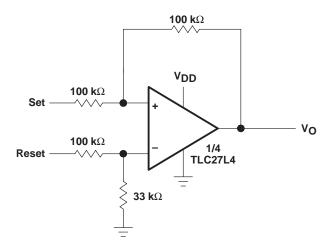
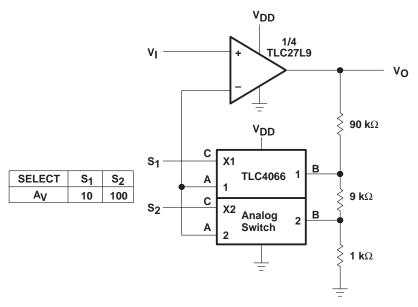


Figure 44. Multivibrator



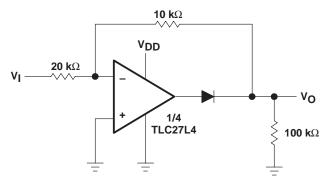
NOTE:  $V_{DD} = 5 \text{ V to } 16 \text{ V}$ 

Figure 45. Set/Reset Flip-Flop



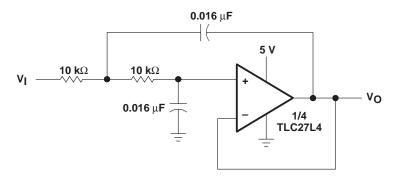
NOTE:  $V_{DD} = 5 V \text{ to } 12 V$ 

Figure 46. Amplifier With Digital Gain Selection



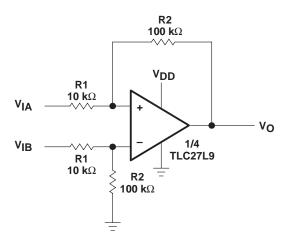
NOTE:  $V_{DD} = 5 \text{ V to } 16 \text{ V}$ 

Figure 47. Full-Wave Rectifier



NOTE: Normalized to FC = 1 kHz and RL = 10 k $\Omega$ 

Figure 48. Two-Pole Low-Pass Butterworth Filter



NOTE:  $V_{DD} = 5 \text{ V to } 16 \text{ V}$  $V_{O} = \frac{R2}{R1} (V_{IB} - V_{IA})$ 

Figure 49. Difference Amplifier





24-Jan-2013

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TLC27L4ACD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4AC	Samples
TLC27L4ACN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4ACN	Samples
TLC27L4ACNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4ACN	Samples
TLC27L4AID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4AI	Samples
TLC27L4AIN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4AIN	Samples
TLC27L4AINE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4AIN	Samples
TLC27L4BCD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	27L4BC	Samples
TLC27L4BCN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4BCN	Samples





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Orderable Device	Status	Package Type		Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
TLC27L4BCNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4BCN	Samples
TLC27L4BID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples
TLC27L4BIDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples
TLC27L4BIDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples
TLC27L4BIDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	27L4BI	Samples
TLC27L4BIN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4BIN	Samples
TLC27L4BINE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4BIN	Samples
TLC27L4CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Samples
TLC27L4CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Samples
TLC27L4CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Samples
TLC27L4CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4C	Samples
TLC27L4CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4CN	Samples
TLC27L4CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L4CN	Samples
TLC27L4CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4	Samples
TLC27L4CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L4	Samples
TLC27L4CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Samples
TLC27L4CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Samples
TLC27L4CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	0 to 70		





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TLC27L4CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Samples
TLC27L4CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	P27L4C	Samples
TLC27L4ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Samples
TLC27L4IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Samples
TLC27L4IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Sample
TLC27L4IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L4I	Sample
TLC27L4IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4IN	Sample
TLC27L4INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L4IN	Sample
TLC27L4IPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sample
TLC27L4IPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sample
TLC27L4IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sample
TLC27L4IPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	P27L4I	Sample
TLC27L4MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27L4MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		
TLC27L4MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		
TLC27L9CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sample
TLC27L9CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sample
TLC27L9CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sample
TLC27L9CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9C	Sample





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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TLC27L9CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L9CN	Samples
TLC27L9CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	TLC27L9CN	Samples
TLC27L9CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9	Samples
TLC27L9CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TLC27L9	Samples
TLC27L9ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Samples
TLC27L9IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Samples
TLC27L9IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Samples
TLC27L9IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC27L9I	Samples
TLC27L9IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L9IN	Samples
TLC27L9INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	TLC27L9IN	Samples
TLC27L9MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	-55 to 125		
TLC27L9MJ	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		
TLC27L9MJB	OBSOLETE	CDIP	J	14		TBD	Call TI	Call TI	-55 to 125		

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



#### **PACKAGE OPTION ADDENDUM**

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

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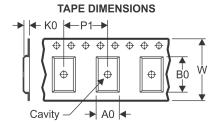
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### PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC27L4ACDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4BCDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4BIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L4CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC27L4CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC27L4IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC27L9CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC27L9CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC27L9IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC27L4ACDR	SOIC	D	14	2500	333.2	345.9	28.6
TLC27L4AIDR	SOIC	D	14	2500	367.0	367.0	38.0
TLC27L4BCDR	SOIC	D	14	2500	367.0	367.0	38.0
TLC27L4BIDR	SOIC	D	14	2500	367.0	367.0	38.0
TLC27L4CDR	SOIC	D	14	2500	333.2	345.9	28.6
TLC27L4CNSR	SO	NS	14	2000	367.0	367.0	38.0
TLC27L4CPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
TLC27L4IPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
TLC27L9CDR	SOIC	D	14	2500	367.0	367.0	38.0
TLC27L9CNSR	SO	NS	14	2000	367.0	367.0	38.0
TLC27L9IDR	SOIC	D	14	2500	367.0	367.0	38.0

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